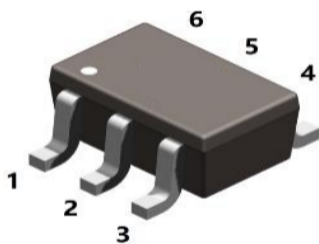


FEATURES

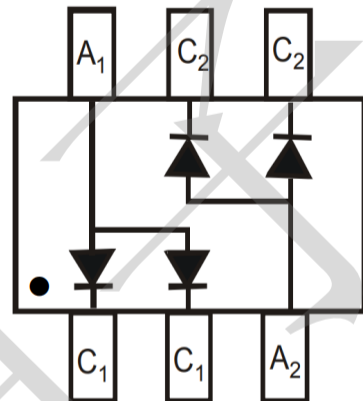
- Fast switching speed.
- For general purpose switching application.
- Ultra-small surface mount package.
- High conductance.



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APPLICATIONS

- For general purpose switching application.



BAW56DW

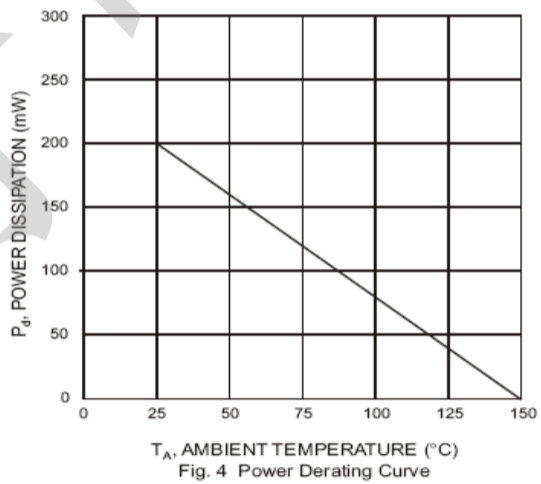
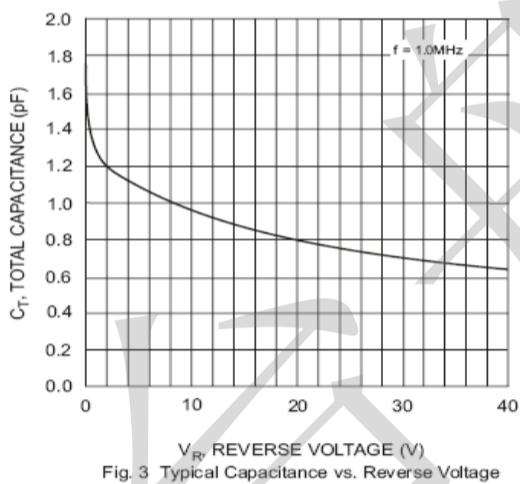
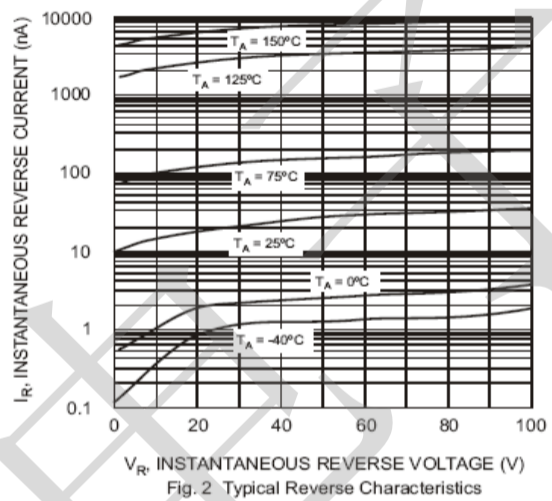
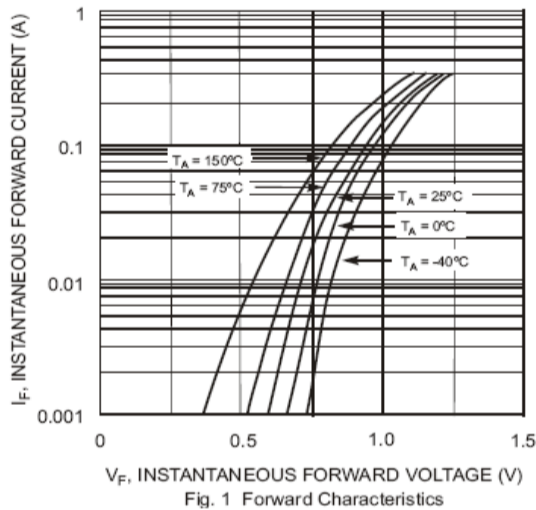
MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Characteristic	Value	Unit
V_{RM}	Non-repetitive peak reverse voltage	100	V
V_{RRM}	Peak repetitive reverse voltage	75	V
V_{RWM}	Working peak reverse voltage		
V_R	DC reverse voltage		
$V_{R(RMS)}$	RMS Reverse voltage	53	V
I_O	Average rectified output current	150	mA
I_{FSM}	Non-Repetitive peak forward surge current		
	@t=1.0μs	2.0	A
	@t=1.0s	1.0	
P_D	Diode Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	625	°C/W
T_j, T_{stg}	Junction and Storage Temperature	-65 to +150	°C

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

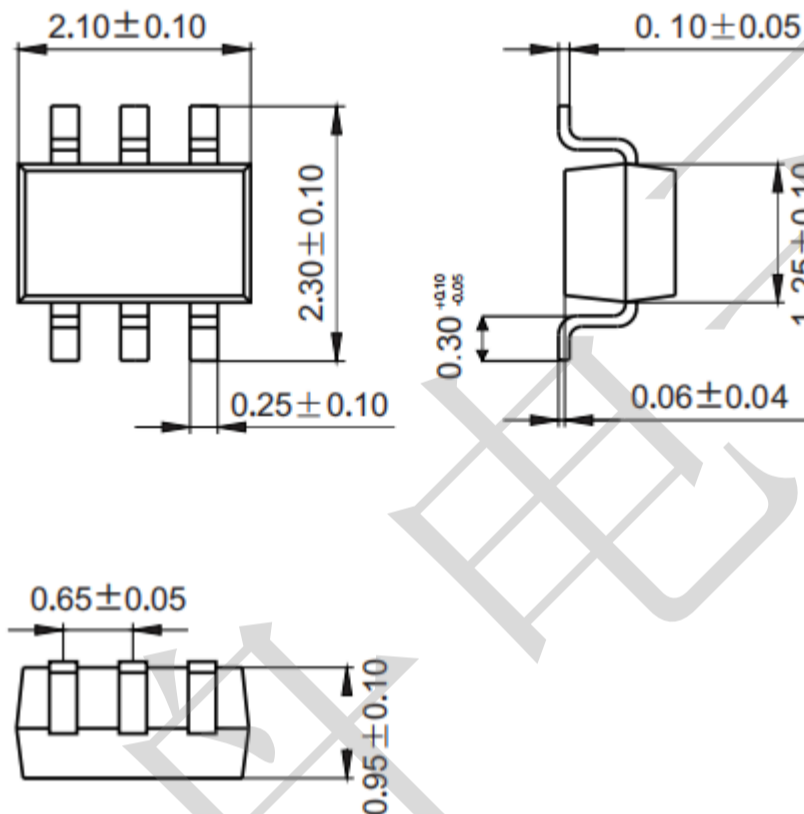
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=2.5\mu A$	75	-	V
Forward voltage	V_F	$I_F=1.0mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$	-	0.715 0.855 1.0 1.25	V
Reverse voltage leakage current	I_R	$V_R=75V$ $V_R=75V, T_j=150^\circ C$ $V_R=25V, T_j=150^\circ C$ $V_R=20V$		2.5 50 30 25	μA μA μA nA
Total Capacitance	C_T	$V_R=0V, f=1.0MHz$	-	2.0	pF
Reverse Recovery time	t_{rr}	$I_F=I_R=10mA, I_{rr}=0.1 \cdot I_R,$ $R_L=100\Omega$	-	4.0	ns

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



Package Outline Dimensions (unit:mm)

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Mounting Pad Layout (unit: mm)

